

# MICROWAVE POWER GaAs FET

# TIM5964-45SL

#### MICROWAVE SEMICONDUCTOR TECHNICAL DATA

#### **FEATURES**

- ·BROAD BAND INTERNALLY MATCHED FET
- ·HIGH POWER

P1dB= 46.5dBm at 5.9GHz to 6.4GHz

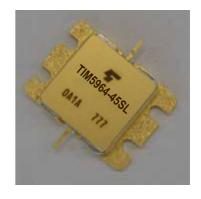
·HIGH GAIN

G1dB= 9.0dB at 5.9GHz to 6.4GHz

**LOW INTERMODULATION DISTORTION** 

IM3= -45dBc at Pout= 35.5dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE



# RF PERFORMANCE SPECIFICATIONS (Ta=25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 9.0A f= 5.9 to 6.4GHz	dBm	46.0	46.5	_
Power Gain at 1dB Gain Compression Point	G1dB		dB	8.0	9.0	_
Drain Current	IDS1		Α	_	9.6	10.8
Gain Flatness	ΔG		dB	_	_	±0.8
Power Added Efficiency	ηadd		%	_	41	_
3rd Order Intermodulation Distortion	IM3	Two-Tone Test Po= 35.5dBm, ∆f= 5MHz (Single Carrier Level)	dBc	-42	-45	
Drain Current	IDS2		Α	_	9.6	10.8
Channel Temperature Rise	ΔTch	(VDS × IDS + Pin – P1dB) × Rth(c-c)	°C	_	_	100

Recommended Gate Resistance(Rg): 28 Ω

# **ELECTRICAL CHARACTERISTICS (Ta=25°C)**

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 11.0A	S	_	8.0	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 170mA	V	-1.0	-2.5	-4.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	Α	_	24	_
Gate-Source Breakdown Voltage	VGSO	IGS= -500μA	V	-5	_	_
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	_	0.8	1.2

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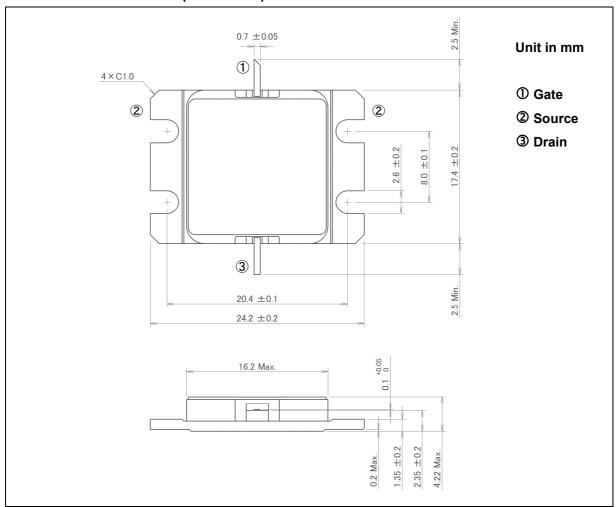
MICROWAVE SEMICONDUCTOR TECHNICAL DATA



# ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	20
Total Power Dissipation (Tc= 25°C)	PT	W	125
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

# PACKAGE OUTLINE (2-16G1B)



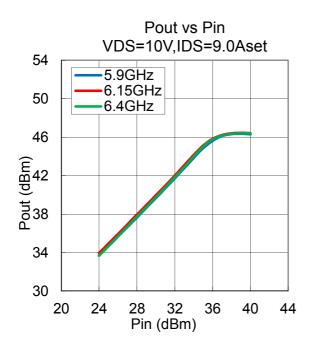
#### HANDLING PRECAUTIONS FOR PACKAGE MODEL

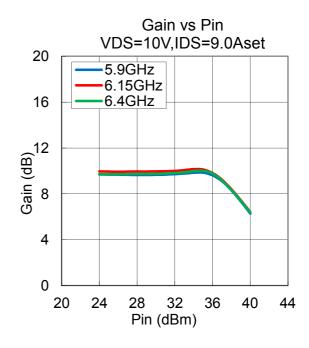
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

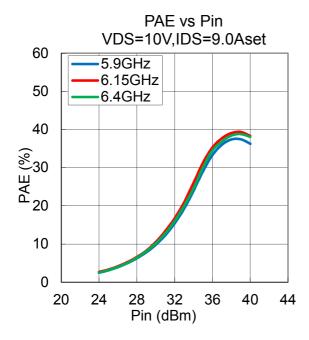
#### TYPICAL RF PERFORMANCE

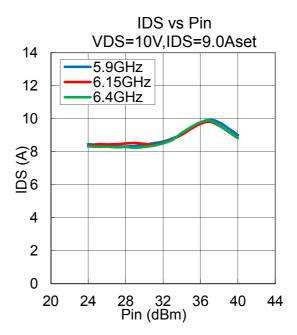
·Pout, Gain, PAE, IDS vs. Pin

VDS= 10 V, IDSset= 9 A, f= 5.9, 6.15, 6.4 GHz, Ta= +25 °C





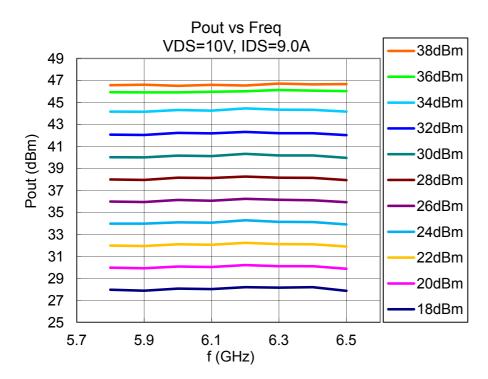






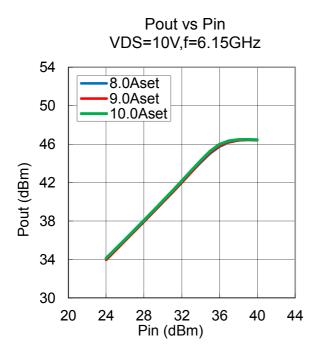
#### ·Pout vs. Frequency

VDS= 10 V, IDSset= 9.0 A, Ta= +25 °C

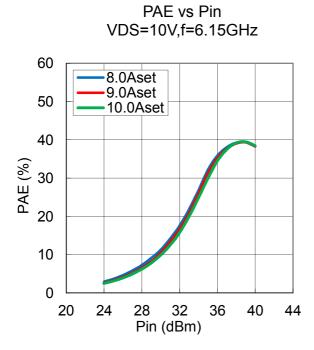


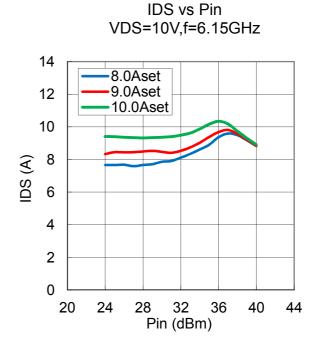
·Pout , Gain , PAE , IDS vs. Pin vs. IDSset

VDS= 10 V, IDSset= 8.0, 9.0, 10.0 A, f= 6.15 GHz, Ta= +25 °C



Gain vs Pin VDS=10V,f=6.15GHz 20 8.0Aset 9.0Aset 10.0Aset 16 12 Gain (dB) 8 4 0 20 24 28 32 36 40 44 Pin (dBm)

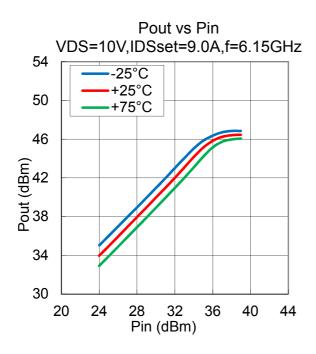


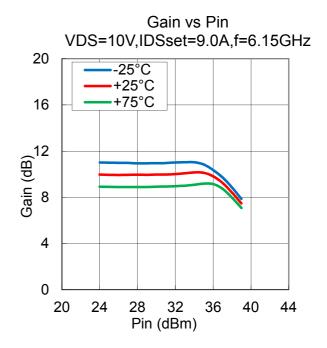


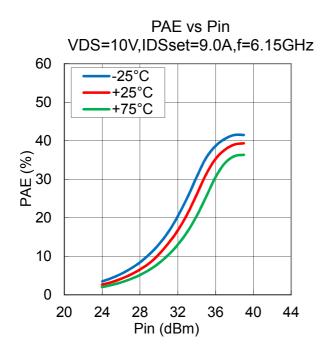


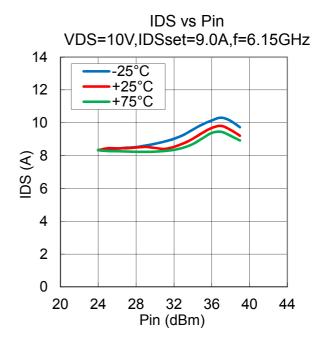
#### ·Pout, Gain, PAE, IDS vs. Pin vs. Temperature

VDS= 10 V, IDSset= 9.0 A, f= 6.15 GHz, Ta= -25, +25, +75 °C











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